

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

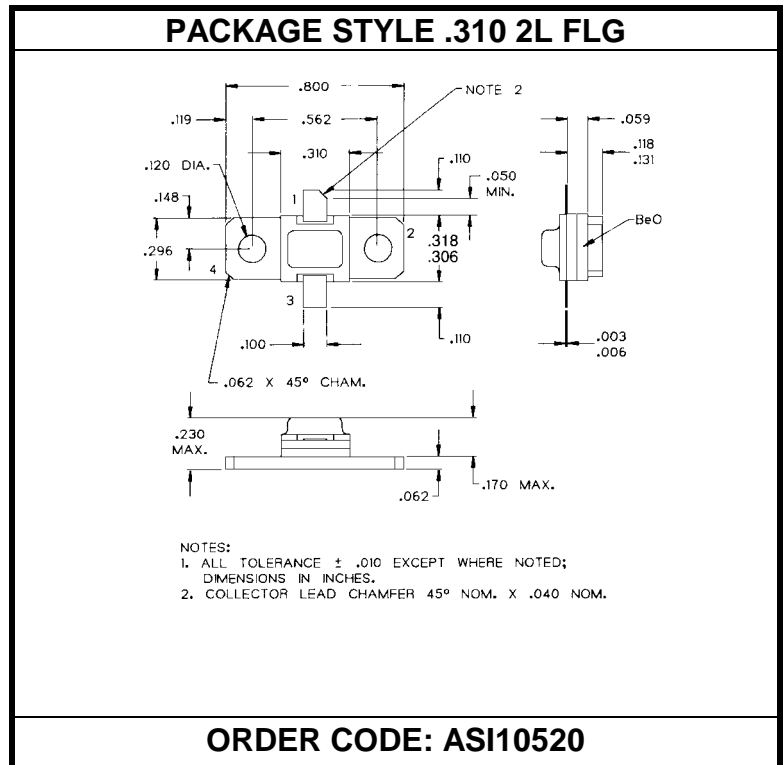
The **ASI ASAT25** is Designed for General Purpose Class Operations up to 1.7 GHz.

**FEATURES:**

- Internal Input/Output Matching Network
- $P_G = 9.0$  dB at 25 W/1.7 GHz
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_C$	2.6 A
$V_{CBO}$	45 V
$V_{CEO}$	12 V
$V_{EBO}$	3.0 V
$P_{DISS}$	50 W @ $T_C = 25$ °C
$T_J$	-65 °C to +200 °C
$T_{STG}$	-65 °C to +150 °C
$\theta_{JC}$	3.5 °C/W


**CHARACTERISTICS**  $T_C = 25$  °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CBO}$	$I_C = 6.0$ mA			45			V
$BV_{CEO}$	$I_C = 6.0$ mA			12			V
$BV_{EBO}$	$I_E = 6.0$ mA			3.0			V
$h_{FE}$	$V_{CE} = 5.0$ V	$I_C = 1.2$ A		15		150	---
$P_G$	$V_{CC} = 28$ V	$P_{OUT} = 25$ W	$f = 1.65$ GHz	9.0			dB
$\eta_C$				50			%